

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	4	("5756400" or ("20020053764")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/10/26 11:35
L2	4	("5756400" or ("20020053674")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/10/26 11:35
S1	2	("20040082186").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/10/16 10:43
S2	6	(@ad<="20021014") and ((dummy or seasoning) with wafer) and clean\$3 and etch\$3 and (deo with duly)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/26 15:10
S3	0	(@ad<="20021014") and ((dummy or seasoning) with wafer) and clean\$3 and etch\$3 and (deo with duly) and (BCI3 or "BCI. sub.3")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/02 14:46
S4	3	(@ad<="20021014") and ((dummy or seasoning) with wafer) and clean\$3 and etch\$3 and (deo with duly) and (metal)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/02 16:39
S5	2	("6872322").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/10/16 14:18
S6	6	("6872322") or ("6765400") or ("6566270").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/10/16 14:20
S7	6	("6872322") or ("6765400") or ("6566270").PN.	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/10/16 14:21
S8	3	("6872322") or ("6765400") or ("6566270").PN.	USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2006/10/16 14:21

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S9	6	(("6872322") or ("6765400") or ("6566270")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/10/16 14:23
S10	2	S8 and tungsten	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/16 14:24
S11	3	(("6872322") or ("5765400") or ("6566270")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2006/10/16 14:25
S12	2	S10 and tungsten	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/16 14:26
S13	3	(("6872322") or ("5756400") or ("6566270")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2006/10/16 14:25
S14	1	S13 and tungsten	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/16 14:26
S15	2	("5756400").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/10/25 17:17
S16	2	("6566270").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/10/25 17:17
S17	3	(("6872322") or ("6765400") or ("6566270")).PN.	USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2006/10/26 09:05
S18	7832	ye.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/26 09:05
S19	175	(@ad<="20021014") and ((dummy or seasoning) with wafer) and ((clean\$3 with chamber) same (Cl2 or "cl.sub.2" or chlorine or fluorine))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/26 15:18

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S20	75	(@ad<="20021014") and ((dummy or seasoning) with wafer) and ((clean\$3 with chamber) same (Cl2 or "cl.sub.2" or chlorine))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/26 16:41
S21	2	("20040082186").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/04/26 16:09
S22	15	(@ad<="20021014") and ((dummy or seasoning) with wafer) and ((clean\$3 with chamber) same ((Cl2 or "cl.sub.2" or chlorine) with (cf4 or "cf.sub.4")))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/27 10:57
S23	66655	(@ad<="20021024") and semiconductor and insulat\$3 and conductive and etch\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/27 11:02
S24	12069	(@ad<="20021024") and "semiconductor layer" and insulat\$3 and conductive and etch\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/30 08:57
S25	3685	(@ad<="20021024") and ("semiconductor layer" same insulat\$3 same conductive) and etch\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/27 11:03
S26	753	(@ad<="20021024") and ("semiconductor layer" same insulator same conductive) and etch\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/25 12:14
S27	2	"20020137352"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/30 08:13
S28	6	(US-20040082186-\$ or US-20020162827-\$ or US-20030222306-\$ or US-20020137352-\$).did. or (US-6566270-\$ or US-6872322-\$).did.	US-PGPUB; USPAT	OR	ON	2007/04/30 08:33
S29	1	S28 and (brom\$4 or bcl\$4)	US-PGPUB; USPAT	OR	ON	2007/04/30 08:33
S30	28	(@ad<="20021024") and (tungsten with etch\$3 with (cl2 or "cl.sub.2") with (SF6 or "sf.sub.6") with (o2 or "o.sub.2" or oxygen))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/30 10:27

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S31	4926	(@ad<="20021024") and ("second conductive" with etch\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/30 10:29
S32	33	(@ad<="20021024") and ("second conductive" with etch\$3 and bromine)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/30 11:22
S33	2	("20050056615").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/04/30 11:22
S34	84	(@ad<="20021014") and ((dummy or seasoning) with wafer with quartz)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/02 14:46
S35	83	(@ad<="20021014") and ((dummy) with wafer with quartz)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/02 14:46
S36	64	(@ad<="20021014") and (("dummy wafer") with quartz)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/02 14:54
S37	3	(@ad<="20021014") and (("dummy wafer") with quartz with clean\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/02 14:49
S38	1	(@ad<="20021014") and (("dummy wafer") with quartz with clean\$4 with etch\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/02 14:49
S39	11	(@ad<="20021014") and (("dummy wafer" with quartz) same etch\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/02 16:32
S40	2	("20020121502").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/05/02 16:32

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S41	2651	(@ad<="20021014") and (etch\$3 with (BCI3 or "BCI.sub.3"))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/02 16:40
S42	24	(@ad<="20021014") and (etch\$3 with conductor with (BCI3 or "BCI.sub.3"))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/02 16:41
S43	2	("20040082186").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/10/25 08:54
S44	49	(@ad<="20021024") and ("semiconductor layer" same insulator same conductive) and ((first near2 etch\$3) same (second near2 etch\$3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/25 12:15
S45	34	(@ad<="20021024") and ("semiconductor layer" same insulator same conductive) and ((first near2 etch\$3) same (second near2 etch\$3)) and gate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/25 12:15